PROCESS CPD76X

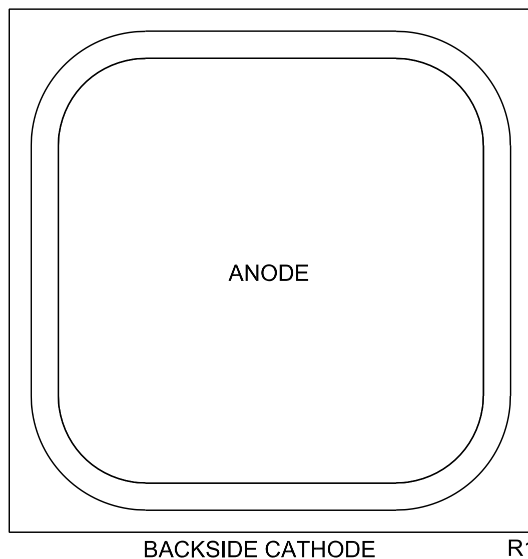
Schottky Diode

1 Amp Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	32 x 32 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	27 x 27 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

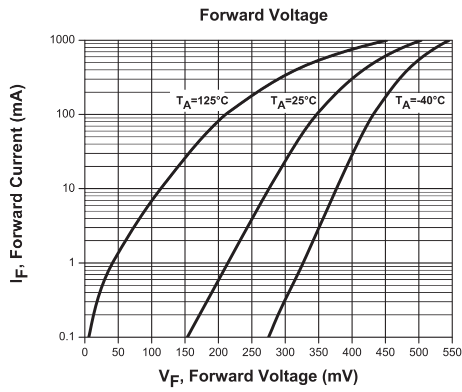
16,276

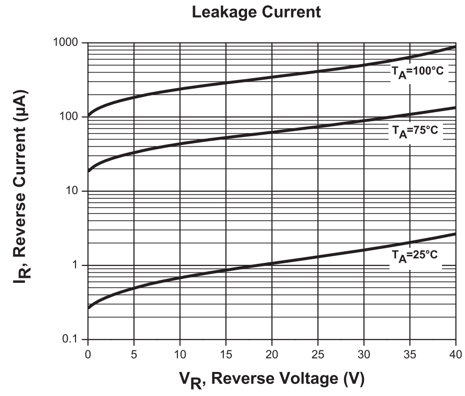
PRINCIPAL DEVICE TYPES

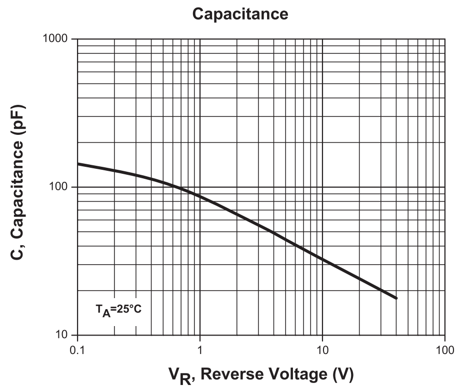
CMLSH1-40
CXSH-4
CTLSH1-40M832D

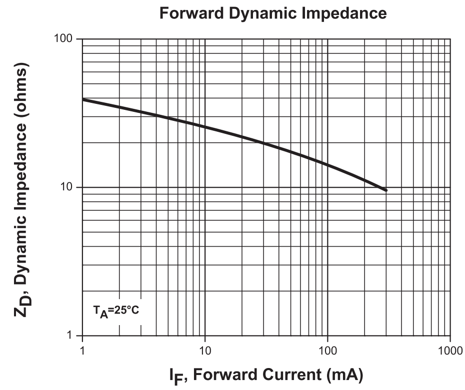
R2 (22-March 2010)

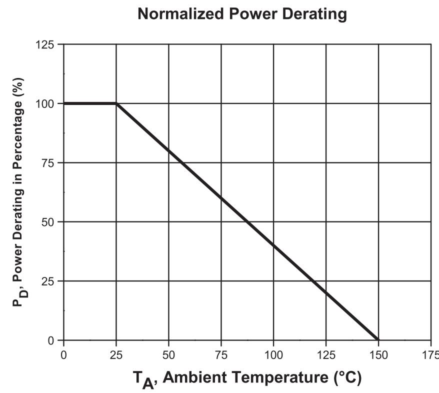
Typical Electrical Characteristics











R2 (22-March 2010)